



40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

| BV _{DSS} | Rds(on) Max | I _D T _C = +25°C | |
|-------------------|-------------------------------|--|--|
| 40V | 1.2mΩ @ V _{GS} = 10V | 225A | |

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable and Robust End Application
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low RDS(ON) Minimizes On State Losses
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES™ DMTH41M2SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

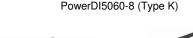
Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine management systems
- Body control electronics
- DC-DC converters

Mechanical Data

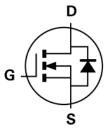
- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



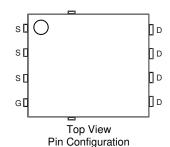




Top View **Bottom View**







Ordering Information (Note 4)

| Part Number | Package | Packing | | |
|-----------------|------------------------|---------|-------------|--|
| rait Nullibei | rackage | Qty. | Carrier | |
| DMTH41M2SPSQ-13 | PowerDI5060-8 (Type K) | 2,500 | Tape & Reel | |

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



TH41M2SS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 22 = 2022) WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|---|-----------------------------------|-------|------------|---|
| Drain-Source Voltage | VDSS | 40 | V | |
| Gate-Source Voltage | Vgss | ±20 | V | |
| Continuous Drain Current, V _{GS} = 10V (Note 6) | $T_C = +25$ °C $T_C = +100$ °C | lo | 225 160 | А |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | I _{DM} | 900 | Α | |
| Continuous Body Diode Forward Current (Note 6) | T _C = +25°C | ls | 200 | Α |
| Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%) | Ism | 900 | Α | |
| Avalanche Current, L = 0.1mH | las | 73 | Α | |
| Avalanche Energy, L = 0.1mH | Eas | 266 | mJ | |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit | |
|--|------------------------|-------------------|-------------|------|
| Total Power Dissipation (Note 5) | $T_A = +25^{\circ}C$ | PD | 3.4 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | RθJA | 44 | °C/W | |
| Total Power Dissipation (Note 6) | T _C = +25°C | PD | 158 | W |
| Thermal Resistance, Junction to Case (Note 6) | | R _θ JC | 0.9 | °C/W |
| Operating and Storage Temperature Range | | TJ, TSTG | -55 to +175 | °C |

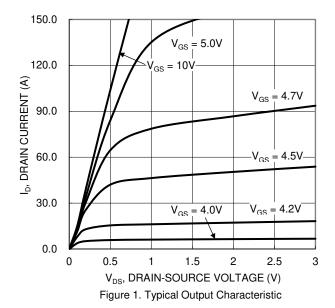
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

| Ohawaatawiatia | Cumphal | M: | T | May | I Incli | Took Condition | |
|-----------------------------------|---------------------|-----|-------|------|---------|--|--|
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
| OFF CHARACTERISTICS (Note 7) | 1 | | 1 | | 1 | | |
| Drain-Source Breakdown Voltage | BVDSS | 40 | | _ | V | $V_{GS} = 0V$, $I_D = 1mA$ | |
| Zero Gate Voltage Drain Current | IDSS | _ | | 1 | μΑ | $V_{DS} = 32V$, $V_{GS} = 0V$ | |
| Gate-Source Leakage | Igss | _ | _ | ±100 | nA | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 2 | _ | 4 | V | $V_{DS} = V_{GS}$, $I_D = 250\mu A$ | |
| Static Drain-Source On-Resistance | RDS(ON) | _ | 0.9 | 1.2 | mΩ | V _{GS} = 10V, I _D = 30A | |
| Diode Forward Voltage | V_{SD} | _ | 0.76 | 1.3 | V | $V_{GS} = 0V, I_{S} = 20A$ | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | • | |
| Input Capacitance | Ciss | _ | 11085 | _ | | V _{DS} = 20V, V _{GS} = 0V, f = 1MHz | |
| Output Capacitance | Coss | _ | 2793 | _ | pF | | |
| Reverse Transfer Capacitance | Crss | _ | 163 | _ | | | |
| Gate Resistance | Rg | _ | 3.64 | _ | Ω | $V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$ | |
| Total Gate Charge | Qg | _ | 138 | _ | | | |
| Gate-Source Charge | Qgs | _ | 53 | _ | nC | $V_{DD} = 20V, I_D = 50A, V_{GS} = 10V$ | |
| Gate-Drain Charge | Qgd | _ | 10 | _ | | | |
| Turn-On Delay Time | td(ON) | _ | 14 | _ | | $V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 50A, R_{g} = 2.5\Omega$ | |
| Turn-On Rise Time | t _R | _ | 19 | | | | |
| Turn-Off Delay Time | tD(OFF) | _ | 90 | _ | ns | | |
| Turn-Off Fall Time | tF | _ | 36 | _ | | | |
| Reverse Recovery Time | trr | _ | 60 | _ | ns | I_ 15A di/dt 100A/us | |
| Reverse Recovery Charge | Qrr | _ | 90 | _ | nC | - I _F = 15A, di/dt = 100A/μs | |

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





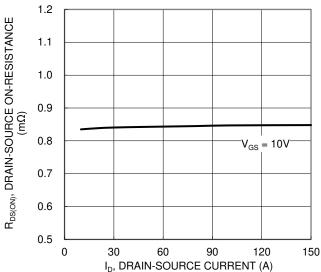


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

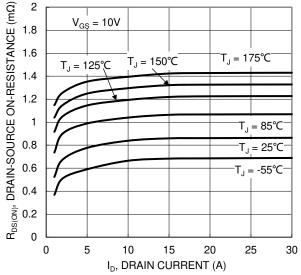


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

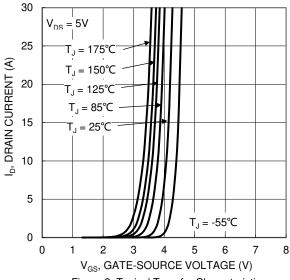
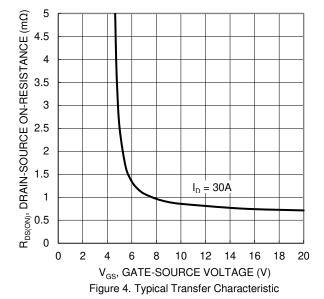


Figure 2. Typical Transfer Characteristic



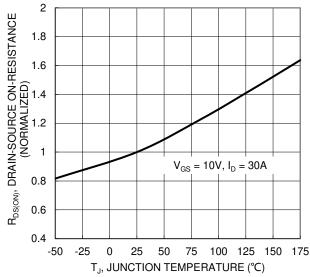


Figure 6. On-Resistance Variation with Temperature



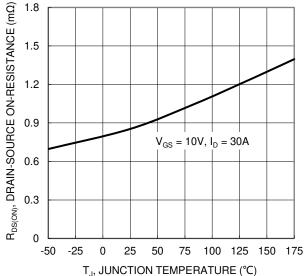


Figure 7. On-Resistance Variation with Temperature

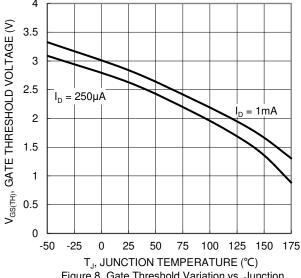


Figure 8. Gate Threshold Variation vs. Junction Temperature

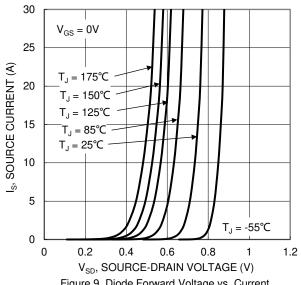
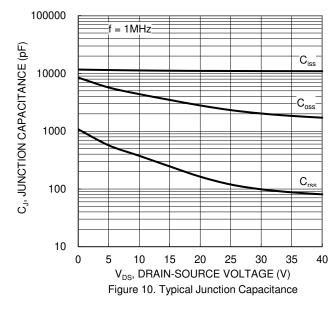
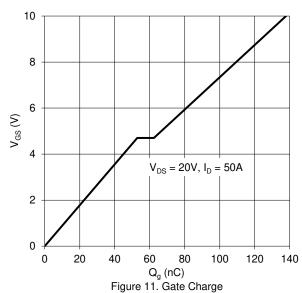
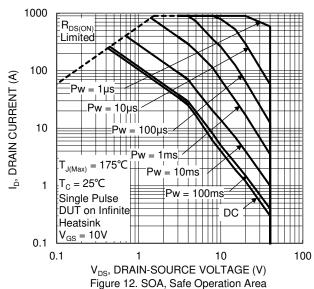


Figure 9. Diode Forward Voltage vs. Current









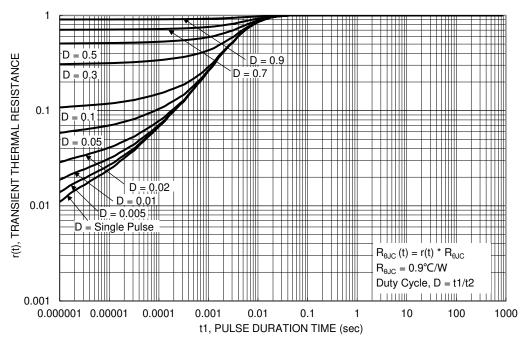


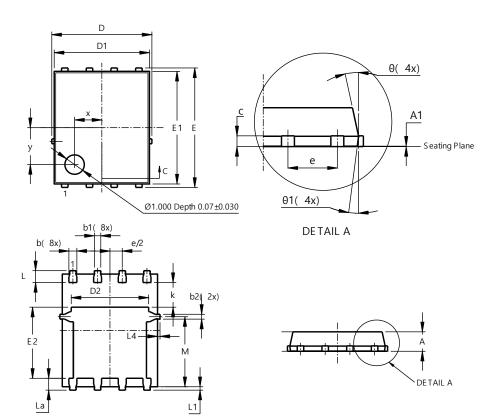
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)

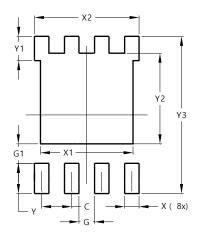


| PowerDI5060-8 | | | | | | |
|----------------------|-------|---------|-------|--|--|--|
| (Type K) | | | | | | |
| Dim | Min | Max | Тур | | | |
| Α | 0.90 | 1.10 | 1.00 | | | |
| A1 | 0 | 0.05 | 0.02 | | | |
| b | 0.33 | 0.51 | 0.41 | | | |
| b1 | 0.300 | 0.366 | 0.333 | | | |
| b2 | 0.20 | 0.35 | 0.25 | | | |
| С | 0.23 | 0.33 | 0.277 | | | |
| D | 5 | .15 BS0 |) | | | |
| D1 | 4.85 | 4.95 | 4.90 | | | |
| D2 | - | - | 3.98 | | | |
| Е | 6 | .15 BS0 |) | | | |
| E1 | 5.75 | 5.85 | 5.80 | | | |
| E2 | 3.56 | 3.725 | 3.66 | | | |
| е | 1 | .27BSC |) | | | |
| k | - | - | 1.27 | | | |
| L | 0.51 | 0.71 | 0.61 | | | |
| La | 0.51 | 0.675 | 0.61 | | | |
| L1 | 0.05 | 0.20 | 0.175 | | | |
| L4 | - | - | 0.125 | | | |
| М | 3.50 | 3.71 | 3.605 | | | |
| Х | - | - | 1.400 | | | |
| у | - | - | 1.900 | | | |
| θ | 10° | 12° | 11° | | | |
| θ1 | 6° | 8° | 7° | | | |
| All Dimensions in mm | | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)



| Dimensions | Value | | |
|------------|---------|--|--|
| | (in mm) | | |
| С | 1.270 | | |
| G | 0.660 | | |
| G1 | 0.820 | | |
| X | 0.610 | | |
| X1 | 3.910 | | |
| X2 | 4.420 | | |
| Y | 1.270 | | |
| Y1 | 1.020 | | |
| Y2 | 3.810 | | |
| Y3 | 6.610 | | |



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